Schottky Barrier Diode

RB481K

●Applications

Low current rectification

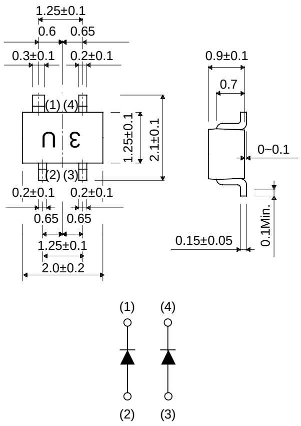
●Features

1) Compact size.
2) High reliability.
3) Extremely low forward voltage.
4) This is a composite component and is ideal for reducing the number of components used.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM : UMD4
EIAJ : SC - 82

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	30	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	0.2	A
Peak forward surge current∗	I_{FSM}	1	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40~+125	°C

∗ 60 Hz for 1 ∿

●Electrical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F1	–	0.18	0.28	V	I_F=1mA
	V_F2	–	0.25	0.33	V	I_F=10mA
	V_F3	–	0.34	0.43	V	I_F=100mA
	V_F4	–	0.40	0.50	V	I_F=200mA
Reverse current	I_R	–	3.6	30	μA	V_R=10V

●**Electrical characteristic curves** (Ta=25°C)

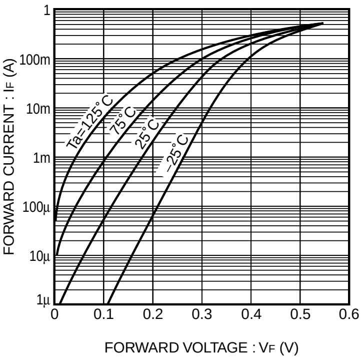


Fig. 1 Forward temperature characteristic

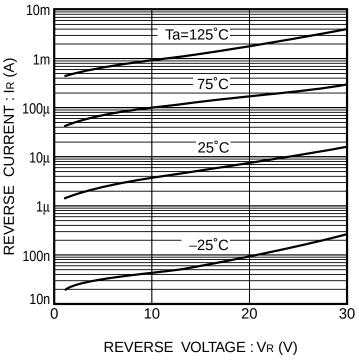


Fig. 2 Reverse temperature characteristic

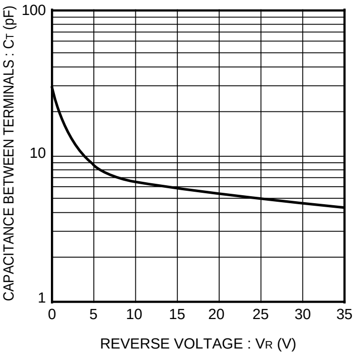


Fig. 3 Capacitance between terminals characteristic